

Lower output capacitance and on resistance. High speed switching. (Turn on time: 0.2ms, Turn off time: 0.08ms).

RF PhotoMOS (AQW22ON)

FEATURES

1. PhotoMOS relay 2-channels (Form A) type with high response speed, low leakage current and low On resistance.

Applicable for 2 Form A use as well as two independent 1 Form A use Compact 8-pin DIP size

The device comes in a compact (W) $6.4\times(L) 9.78\times(H) 3.9 \text{ mm}$ (W) $.252\times(L)$ $.385\times(H) .154 \text{ inch}$, 8-pin DIP size (through hole terminal type).

4. Low capacitance between output terminals ensures high response speed:

speed:

The capacitance between output terminals is small, typically 10 pF. This enables for a fast operation speed of 200 μ s.

5. High sensitivity and low On resistance:

Maximum 0.07 A of load current can be controlled with input current of 5 mA. The On resistance is less than our

conventional models. With no metallic contacts, the PhotoMOS relay has stable switching characteristics.

6. Low-level off state leakage current: The SSR has an off state leakage current of several milliamperes, whereas the PhotoMOS relay has only 30 pA even with the rated load voltage of 200 V (AQW227N).

7. Controls low-level analog signals: PhotoMOS relay features extremely low closed-circuit offset voltages to enable control of small analog signals without distortion.

8. Low terminals electromotive force: (approx. 1 μ V)

TYPICAL APPLICATIONS

- Measuring equipment
- Scanner, IC checker, Board tester

TYPES

Туре	Output rating*			Par	Packing quantity			
			Through hole terminal	Surface-mount terminal				
	Load voltage	Load current			Tape and reel packing style			Tape and reel
			Tube packing style		Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side	Tube	
AC/DC type	200 V	50 mA	AQW227N	AQW227NA	AQW227NAX	AQW227NAZ	1 tube contains 40 pcs.	1,000 pcs.
	400 V	40 mA	AQW224N	AQW224NA	AQW224NAX	AQW224NAZ	1 batch contains 400 pcs.	

*Indicate the peak AC and DC values.

Note: For space reasons, the package style indicator "X" or "Z" are not marked on the relay.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

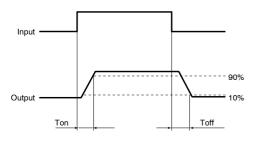
Item		Symbol	AQW227N(A)	AQW224N(A)	Remarks
Input	LED forward current	lf	50 mA		
	LED reverse voltage	Vr	5 V		
	Peak forward current	IFP	1 A		f = 100 Hz, Duty factor = 0.1%
	Power dissipation	Pin	75 mW		
Output	Load voltage (peak AC)	VL	200 V	400 V	
	Continuous load current	١L	0.05 A (0.07 A)	0.04 A (0.05 A)	Peak AC, DC (): in case of using only 1 channel
	Peak load current	Іреак	0.15 A	0.12 A	A connection: 100 ms (1 shot), $V_L = DC$
	Power dissipation	Pout	800 mW		
Total power dissipation		Ρτ	850 mW		
I/O isolation voltage		Viso	1,500 V AC		
Temperature limits	Operating	Topr	−40°C to +85°C −40°F to +185°F		Non-condensing at low temperatures
	Storage	Tstg	-40°C to +100°C -40°F to +212°F		

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 Electrical characteristics (Ambient temperature: 25°C 77°F 	-)
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Item				Symbol	AQW227N(A)	AQW224N(A)	Remarks
Input	LED operate current		Typical	1_	0.9 mA		I∟ = Max.
		e current	Maximum	Fon	3.0 mA		= IL = Max.
	LED turn off current Minimum		Minimum	Foff	0.4 mA		IL = Max.
	Typica			IFott	0.8 mA		IL = IVIAX.
	Typical			VF	1.25 V (1.14 V at I⊧ = 5 mA)		l⊧ = 50 mA
	LED dropout voltage		Maximum	VF	1.	1.5 V	
Output	On resistance		Typical		30 Ω	70 Ω	l⊧ = 5 mA
			Maximum	Ron	50 Ω	100 Ω	I∟ = Max. Within 1 s on time
	Output capacitance		Typical	0	10 pF		$I_{F} = 0$ $V_{B} = 0$ $f = 1 MHz$
			Maximum	Cout	15 pF		
	Off state leakage current		Maximum	lleak	10 nA		I⊧ = 0 V∟ = Max.
Transfer characteristics	Switching speed	Turn on time*	Typical	Ton	0.20 ms		I⊧ = 5 mA I∟ = Max.
			Maximum	Ion	0.5 ms		
		Turn off time*	Typical	Toff	0.08 ms		I⊧ = 5 mA I∟ = Max.
			Maximum	IOT	0.2 ms		
	I/O capacitance		Typical	Ciso —	0.8 pF		f = 1 МНz Vв = 0
			Maximum	CISO	1.5 pF		
	Initial I/O isc	lation resistance	Minimum	Riso	1,000 MΩ		500 V DC
Note: Recomme	Type of connectio						

*Turn on/Turn off time

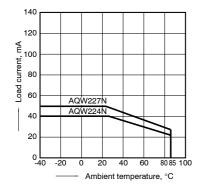


Dimensions Schematic and Wiring Diagrams ■ Cautions for Use

REFERENCE DATA

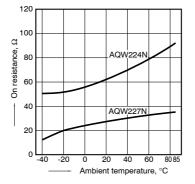
1. Load current vs. ambient temperature characteristics

Allowable ambient temperature: -40°C to +85°C -40°F to +185°F



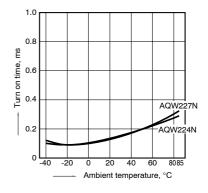
2. On resistance vs. ambient temperature characteristics

Measured portion: between terminals 5 and 6, 7 and 8; LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)

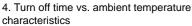


3. Turn on time vs. ambient temperature characteristics

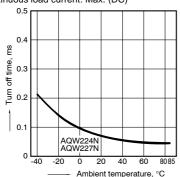
LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)







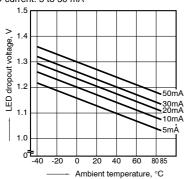
LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



7. LED dropout voltage vs. ambient temperature characteristics

Sample: All types;

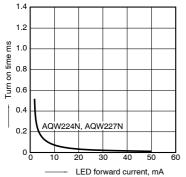
LED current: 5 to 50 mA



10. LED forward current vs. turn on time characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Load voltage: Max. (DC); Continuous load current: Max. (DC);

Ambient temperature: 25°C 77°F

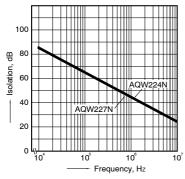


13. Isolation characteristics

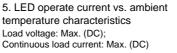
(50 Ω impedance)

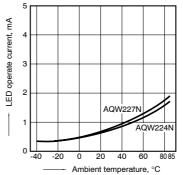
Measured portion: between terminals 5 and 6, 7 and 8;

Ambient temperature: 25°C 77°F



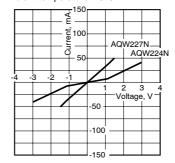
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8. Voltage vs. current characteristics of output at MOS portion

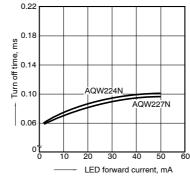
Measured portion: between terminals 5 and 6, 7 and 8; Ambient temperature: 25°C 77°F



11. LED forward current vs. turn off time characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Load voltage: Max. (DC); Continuous load current: Max. (DC);

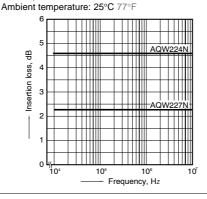
Ambient temperature: 25°C 77°F



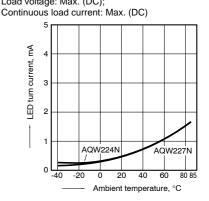
14. Insertion loss characteristics

(50 Ω impedance)

Measured portion: between terminals 5 and 6, 7 and 8;

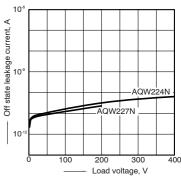


6. LED turn off current vs. ambient temperature characteristics Load voltage: Max. (DC);



9. Off state leakage current Measured portion: between terminals 5 and 6, 7 and 8;

Ambient temperature: 25°C 77°F



12. Applied voltage vs. output capacitance characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Frequency: 1 MHz, 30 mVrms; Ambient temperature: $25^{\circ}C$ 77°F

